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PATENT APPLICATION
Do. No. 4591-222

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Woon-Kyung LEE Confirmation No. 9003
Serial No. 09/995,299 Examiner: Vu, David
Filed: November 27, 2001 Group Art Unit: 2818
For: A METHOD OF FABRICATING A FLASH MEMORY DEVICE

BOX NON FEE AMENDMENT
Assistant Commissioner for Patents
Washington, D.C. 20231

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J. Carter
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RESPONSE TO OFFICE ACTION

Responsive to the Office Action, dated December 18, 2002, please amend the application as follows.

IN THE CLAIMS

Please replace the claims with the following set, in which claims 1 and 12 have been amended and claims 2 and 3 have been cancelled.

1. A method of fabricating a flash memory device having a cell array region and a peripheral circuit region, the method comprising:

forming a device isolation layer at a predetermined region of a semiconductor substrate to define at least one first active region in the cell array region and a second active region in the peripheral circuit region;

forming a floating gate pattern covering the first active region and a gate conductive layer covering the peripheral circuit region;

forming a tunnel oxide layer interposed between the floating gate pattern and the first active region;

forming a gate oxide layer interposed between the gate conductive layer and the second active region;

implanting impurity ions into the first and second active regions prior to formation of the tunnel oxide layer and the gate oxide layer;